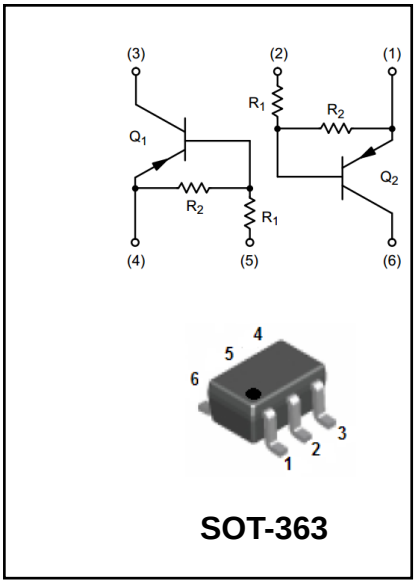
DTA114EDW

Dual Digital Transistor(PNP+PNP)

Features

- Epitaxial Planar Die Construction.
- Complementary NPN Types Available(DTC).
- Built-in Biasing Resistors,R1=R2.
- Also Available in Lead Free Version.



SOT-363

Mechanical Data

- Case: SOT-363.
- Molding compound, UL flammability classification rating 94V-0.
- Terminals: Matte tin plated leads, solderable per MIL-STD-202, Method 208.

Ordering Information

Part Number	Package	Shipping	Marking Code
DTA114EDW	SOT-363	3000 pcs / Tape & Reel	14

Maximum Ratings (@T_A=25℃ unless otherwise specified)

Symbol	Parameter	Value	Units
MAXIMUM RATINGS			
V_{CC}	Supply Voltage	-50	V
V_{IN}	Input Voltage	+10 to -40	V
I_O	Output Current	-50	mA
I_C	Collector Current	-100	mA
Thermal Characteristic			
P_D	Total Power Dissipation, T_a≤25℃	150	mW
T_J	Junction Temperature	150	℃
T_{STG}	Storage Temperature Range	-55 to +150	℃

Electrical Characteristics (@TA=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Input Voltage	$V_{I(off)}$	V_{CC}=-5V,I_O=-100μA	-0.5	-1.1	-	V
	$V_{I(on)}$	V_O=-0.3V,I_O=-10mA	-	-1.9	-3	V
Output Voltage	$V_{O(on)}$	Io=-10mA, I_I=-0.5mA	-	-0.1	-0.3	V
Input Current	I_I	V_I=-5V	-	-	-0.88	mA
Output Current	$I_{O(off)}$	V_{CC}=-50V, V_I=0V	-	-	-0.5	uA
DC Current Gain	G_I	V_O=-5V, I_O=-5mA	30	-	-	-
Input Resistor	R_1		7	10	13	kΩ
Resistance Ratio	R_2/R_1		0.8	1	1.2	-
Gain-Bandwidth Product	f_T	V_{CE}=-10V,I_E=5mA, f=100MHz	-	250	-	MHz

Ratings and Characteristic Curves (T_A=25℃ unless otherwise noted)

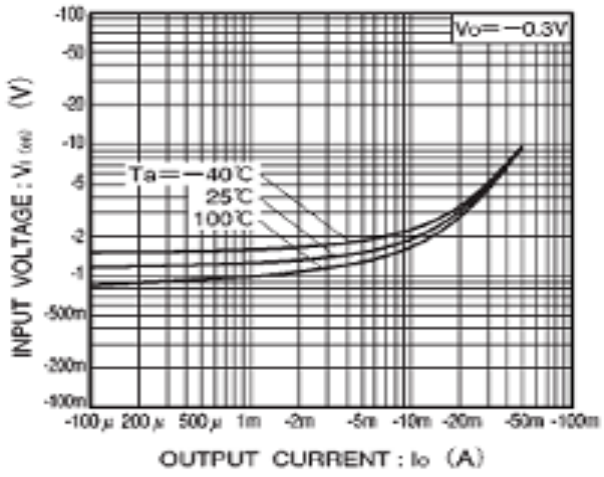


Fig.1 Input voltage vs. output current (ON characteristics)

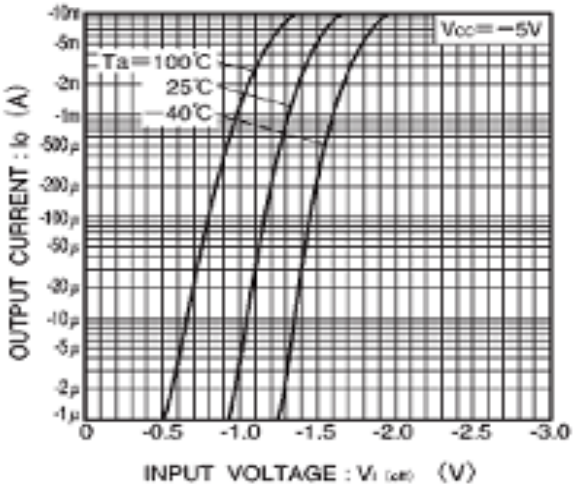


Fig.2 Output current vs. input voltage (OFF characteristics)

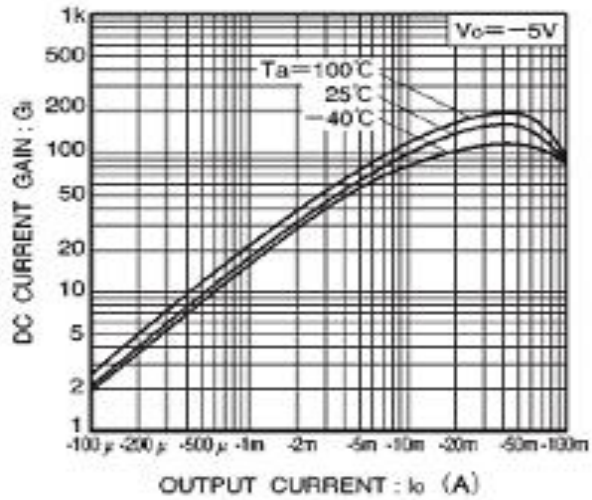


Fig.3 DC current gain vs. output current

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Package Outline Dimensions(unit:mm)

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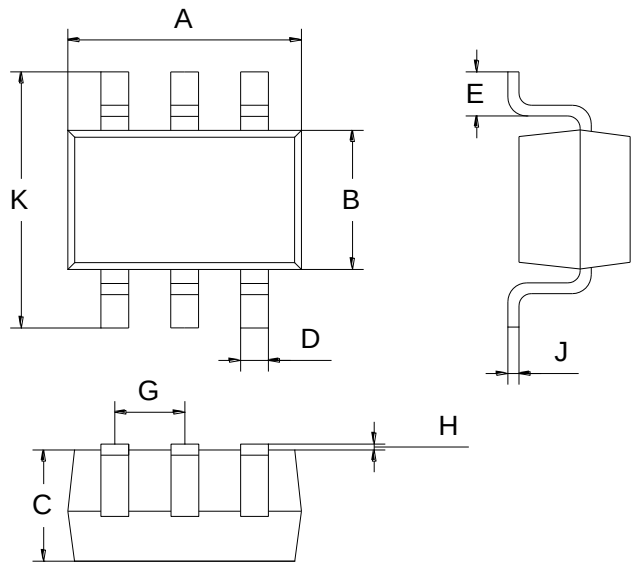

SOT-363		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

SOLDERING FOOTPRINT(unit:mm)